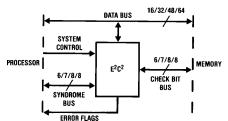


DP8400-2—E²C² Expandable Error Checker/Corrector

General Description

The DP8400-2 Expandable Error Checker and Corrector (E²C²) aids system reliability and integrity by detecting errors in memory data and correcting single or double-bit errors. The E²C² data I/O port sits across the processormemory data bus as shown, and the check bit I/O port connects to the memory check bits. Error flags are provided, and a syndrome I/O port is available. Fabricated using high speed Schottky technology in a 48-pin dual-in-line package, the DP8400-2 has been designed such that its internal delay times are minimal, maintaining maximum memory performance.



TI /F/6899_

For a 16-bit word, the DP8400-2 monitors data between the processor and memory, with its 16-bit bidirectional data bus connected to the memory data bus. The DP8400-2 uses an encoding matrix to generate 6 check bits from the 16 bits of data. In a WRITE cycle, the data word and the corresponding check bits are written into memory. When the same location of memory is subsequently read, the E²C² generates 6 new check bits from the memory data and compares them with the 6 check bits read from memory to create 6 syndrome bits. If there is a difference (causing some syndrome bits to go high), then that memory location contains an error and the DP8400-2 indicates the type of error with 3 error flags. If the error is a single data-bit error, the DP8400-2 will automatically correct it.

The DP8400-2 is easily expandable to other data configurations. For a 32-bit data bus with 7 check bits, two DP8400-2s can be used in cascade with no other ICs. Three DP8400-2s can be used for 48 bits, and four DP8400-2s for 64 data bits, both with 8 check bits. In all these configurations, single and double-error detection and single-error correction are easy to implement.

When the memory is more unreliable, or better system integrity is preferred, then in any of these configurations, double-error correction can be performed. One approach requires a further memory WRITE-READ cycle using complemented data and check bits from the DP8400-2. If at least one of the two errors is a hard error, the DP8400-2 will correct both errors. This implementation requires no more

memory check bits or DP8400-2s than the single-error correct configurations.

The DP8400-2 has a separate syndrome I/O bus which can be used for error logging or error management. In addition, the DP8400-2 can be used in BYTE-WRITE applications (for up to 72 data bits) because it has separate byte controls for the data buffers. In 16 or 32-bit systems, the DP8400-2 will generate and check system byte parity, if required, for integrity of the data supplied from or to the processor. There are three latch controls to enable latching of data in various modes and configurations.

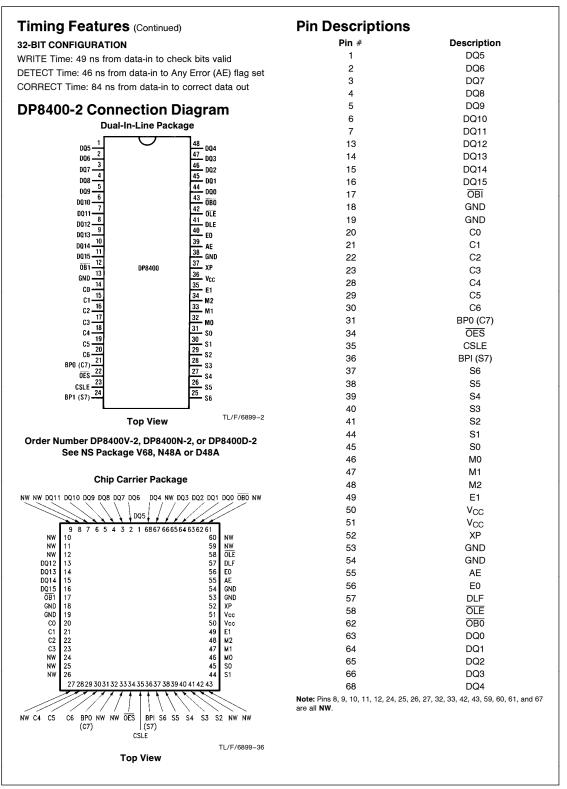
Operational Features

- Fast single and double-error detection
- Fast single-error correction
- Double-error correction after catastrophic failure with no additional ICs or check bits
- Functionally expandable to 100% double-error correct capability
- Functionally expandable to triple-error detect
- Directly expandable to 32 bits using 2 DP8400-2s only
- Directly expandable to 48 bits using 3 DP8400-2s only
- Directly expandable to 64 bits using 4 DP8400-2s only
- Expandable to and beyond 64 bits in fast configuration with extra ICs
- 3 error flags for complete error recording
- 3 latch enable inputs for versatile control
- Byte parity generating and checking
- Separate byte controls for outputting data in BYTE-WRITE operation
- Separate syndrome I/O port accessible for error logging and management
- On-chip input and output latches for data bus, check bit bus and syndrome bus
- Diagnostic capability for simulating check bits
- Memory check bit bus, syndrome bus, error flags and internally generated syndromes available on the data bus
- Self-test of E²C² on the memory card under processor control
- Full diagnostic check of memory with the E²C²
- Complete memory failure detectable
- Power-on clears data and syndrome input latches

Timing Features

16-BIT CONFIGURATION

WRITE Time: 29 ns from data-in to check bits valid
DETECT Time: 21 ns from data-in to Any Error (AE) flag set
CORRECT Time: 44 ns from data-in to correct data out



Pin Definitions See Figure 1 for abbreviations

 V_{CC} , GND, GND: 5.0V $\pm 5\%$. The 3 supply pins have been assigned to the center of the package to reduce voltage drops, both DC and AC. Also there are two ground pins to reduce the low-level noise. The second ground pin is located two pins from V_{CC} , so that decoupling capacitors can be inserted directly next to these pins. It is important to adequately decouple this device, due to the high switching currents that will occur when all 16 data bits change in the same direction simultaneously. A recommended solution would be a 1 μF multilayer ceramic capacitor in parallel with a low-voltage tantalum capacitor, both connected close to pins 36 and 38 to reduce lead inductance.

DQ0-DQ15: Data I/O port. 16-bit bidirectional data bus which is connected to the input of DIL0 and DIL1 and the output of DOB0 and DOB1, with DQ8-DQ15 also to CIL.

C0-C6: Check-bit I/O port. 7-bit bidirectional bus which is connected to the input of the CIL and the output of the COB. COB is enabled whenever M2 is low.

S0–S6: Syndrome I/O port. 7-bit bidirectional bus which is connected to the input of the SIL and the output of the SOB. **DLE:** Input data latch enable. When high, DIL0 and DIL1 outputs follow the input data bus. When low, DIL0 and DIL1 latch the input data.

CSLE: Input check bit and syndrome latch enable. When high, CIL and SIL follow the input check and syndrome bits. When low, CIL and SIL latch the input check and syndrome bits. If $\overline{\text{OES}}$ is low, SIL remains latched.

OLE: Output latch enable. <u>OLE</u> enables the internally generated data to DOL0, and DOL1, COL and SOL when low, and latches when high.

XP: Multi-expansion, which feeds into a three-level comparator. With XP at 0V, only 6 or 7 check bits are available for expansion up to 40 bits, allowing byte parity capability. With XP open or at V_{CC} , expansion beyond 40 bits is possible, but byte parity capability is no longer available. When XP is at V_{CC} , CG6 and CG7, the internally generated upper two check bits, are set low. When XP is open, CG6 and CG7 are set to word parity.

BP0 (C7): When XP is at 0V, this pin is byte-0 parity I/O. In the Normal WRITE mode, BP0 receives system byte-0 parity, and in the Normal READ mode outputs system byte-0 parity. When XP is open or at $V_{\rm CC}$, this pin becomes C7 I/O, the eighth check bit for the memory check bits, for 48-bit expansion and beyond.

BP1 (S7): When XP is at 0V, this pin is byte-1 parity I/O. In the Normal WRITE mode, BP1 receives system byte-1 parity, and in the Normal READ mode outputs system byte-1 parity. When XP is open or at V_{CC} , this pin becomes S7 I/O, the eight syndrome bit for 48-bit expansion and beyond.

AE: Any error. In the Normal READ mode, when low, AE indicates no error and when high, indicates that an error has occurred. In any WRITE mode, AE is permanently low.

E0: In the Normal READ mode, E0 is high for a single-data error, and low for other conditions. In the Normal WRITE mode, E0 becomes $\overline{\text{PE0}}$ and is low if a parity error exists in byte-0 as transmitted from the processor.

E1: In the Normal READ mode, E1 is high for a single-data error or a single check bit error, and low for no error and double-error. In the Normal WRITE mode, E1 becomes $\overline{\text{PE1}}$ and is low if a parity error exists in byte-1 as transmitted from the processor.

OBO, OB1: Output byte-0 and output byte-1 enables. These inputs, when low, enable DOL0 and DOL1 through DOB0 and DOB1 onto the data bus pins DQ0-DQ7 and DQ8-DQ15. When OB0 and OB1 are high the DOB0, DOB1 outputs are TRI-STATE®.

ŌES: Output enables syndromes. I/O control of the syndrome latches. When high, SOB is TRI-STATE and external syndromes pass through the syndrome input latch with CSLE high. When OES is low, SOB is enabled and the generated syndromes appear on the syndrome bus, also CSLE is inhibited internally to SIL.

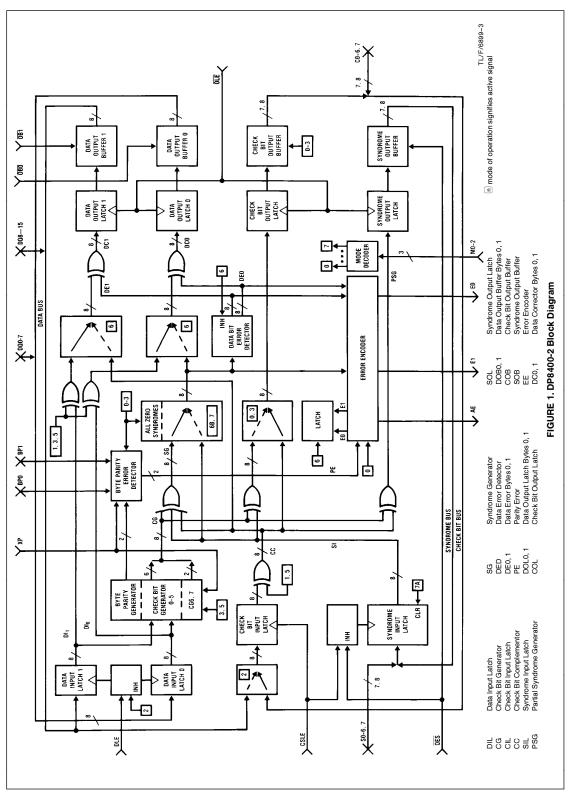
M0, M1, M2: Mode control inputs. These three controls define the eight major operational modes of the DP8400-2. Table III depicts the modes.

System Write (Figure 2a)

The Normal WRITE mode is mode 0 of Table III. Referring to the block diagram in Figure 9a and the timing diagram of Figure 9b, the 16 bits of data from the processor are enabled into the data input latches, DILO and DIL1, when the input data latch enable (DLE) is high. When this goes low, the input data is latched. The check bit generator (CG) then produces 6 parity bits, called check bits. Each parity bit monitors different combinations of the input data-bits. In the 16-bit configuration, assuming no syndrome bits are being fed in from the syndrome bus into the syndrome input latch, the 6 check bits enter the check bit output latch (COL), when the output latch enable OLE is low, and are latched in when OLE goes high. Whenever M2 (READ/WRITE) is low, the check bit output buffer COB always enables the COL contents onto the external check bit bus. Also the data error decoder (DED) is inhibited during WRITE so no correction can take place. Data output latches DOL0 and DOL1, when enabled with OLE, will therefore see the contents of DILO and DIL1. If valid system data is still on the data bus, a memory WRITE will write to memory the data on the data bus and the check bits output from COB. If the system has vacated the data bus, output enables (OBO and OB1) must be set low so that the original data word with its 6 check bits can be written to memory.

System Read

There are two methods of reading data: the error monitoring method (Figure 2b), and the always correct method (Figure 2c). Both require fast error detection, and the second, fast correction. With the first method, the memory data is only monitored by the E2C2, and is assumed to be correct. If there is an error, the Any Error flag (AE) goes high, requiring further action from the system to correct the data. With the always correct method, the memory data is assumed to be possibly in error. Memory data is removed and the corrected, or already correct, data is output from the E2C2 by enabling OB1 and OB0. To detect an error (referring to Figures 10a and 10b) first DLE and CSLE go high to enter data bits and check bits from memory into DIL0, DOL1 and CIL. The 6 check bits generated in CG from DIL0 and DOL1 are then compared with CIL to generate syndromes on the internal syndrome bus (SG). Any bit or bits of SG that go high indicate an error to the error encoder (EE).



System Diagrams—Modes of Operation

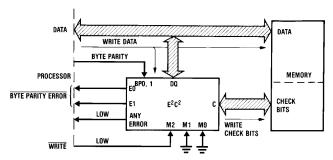


FIGURE 2a. Normal WRITE Mode with E²C²

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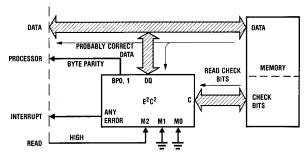


FIGURE 2b. Normal READ Mode, Error Monitoring Method with E²C²

TL/F/6899-5

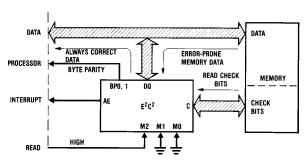


FIGURE 2c. Normal READ Mode, Always Correct Method with E²C²

System Read (Continued)

If data correction is required $\overline{OB0}$ and $\overline{OB1}$ must be set low (after memory data has been disabled) to enable data output buffers DOB0 and DOB1. The location of any data bit error is determined by the data error decoder (DED), from the syndrome bits. The bit in error is complemented in the DOL for correction. The other 15 bits from DED pass the DIL contents directly to the DOL, so that DOL now contains corrected data.

Error Determination

The three error flags, for a 16-bit example, are decoded from the internally generated syndromes as shown in *Figure 3*. First, if any error has occurred, the generated check bits will be different from the memory check bits, causing some of the syndrome bits to go high. By OR-ing the syndrome bits, the output will be an indication of any error.

If there is a single-data error, then (from the matrix in Table IV) it can be seen that any data error causes either 3 or 5 syndrome bits to go high. 16 AND gates decode which bit is in error and the bit in error is XOR-ed with the corresponding bit of the DIL to correct it, whereas the other 15 decoder outputs are low, causing the corresponding 15 bits in DIL to transfer to DOL directly. DOL now contains corrected data. The 16 AND gate outputs are OR-ed together causing E0 to go high, so that E0 is the single-data-error indication. If the error is a double-error, then either 2, 4 or 6 of the syndrome bits will be high. The syndromes for two errors (including

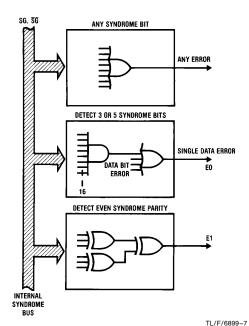


FIGURE 3. Error Encoder

one or two check bit errors) are the two sets of syndromes for each individual error bit, XOR-ed together. By performing a parity check on the syndrome bits, flag E1 will indicate even/odd parity. If there is still an error, but it is not one of these errors, then it is a detectable triple-bit error. Some triple-bit errors are not detectable as such and may be interpreted as single-bit errors and falsely corrected as single-data errors. This is true for all standard ECC circuits using a Modified Hamming-code matrix. The DP8400-2 is capable, with its Rotational Syndrome Word Generator matrix, of determining all triple-bit errors using twice as many DP8400-2s and twice as many check bits.

Error Flags

Three error flags are provided to allow full error determination. Table I shows the error flag outputs for the different error types in Normal READ mode. If there is an error, then ANY ERROR will go high, at a time $t_{\mbox{\scriptsize DEV}}$ (*Figure 10b*) after data and check bits are presented to the DP8400-2. The other two error flags E0 and E1 become valid $t_{\mbox{\scriptsize DE0}}$ and $t_{\mbox{\scriptsize DE1}}$

The error flags differentiate between no error, single check bit error, single data-bit error, double-bit error. Because the DP8400-2 can correct double errors, it is important to know that two errors have occurred, and not just a multiple-error indication. The error flags will remain valid as long as DLE and CSLE are low, or if DLE is high, and data and check bits remain valid

Byte Parity Support

Some systems require extra integrity for transmission of data between the different cards. To achieve this, individual byte parity bits are transmitted with the data bits in both directions. The DP8400-2 offers byte parity support for up to 40 data bits. If the processor generates byte parity when transferring information to the memory, during the WRITE cycle, then each byte parity bit can be connected to the corresponding byte parity I/O pin on the DP8400-2, either BP0 or BP1. The DP8400-2 develops its own internal byte parity bits from the two bytes of data from the processor, and compares them with BP0 and BP1 using an exclusive-OR for both parities. The output of each exclusive-OR is fed to the error flags E0 and E1 as $\overline{\text{PE0}}$ and $\overline{\text{PE1}},$ so that a byte parity error forces its respective error flag low, as in Table II. These flags are only valid for the Normal WRITE (mode 0) and XP at 0V. The DP8400-2 checks and generates even byte parity.

When transferring information from the memory to the processor, the DP8400-2 receives the memory data, and outputs the corresponding byte parity bits on BP0 and BP1 to the processor. The processor block can then check data integrity with its own byte parity generator. If in fact memory data was in error, the DP8400-2 derives BP0 and BP1 from the corrected data, so when corrected data is output from the DP8400-2, the processor will not detect a byte parity error. During the read mode, DP8400-2 corrects single data bit error and also its parity.

TABLE I. Error Flags After Normal Read (Mode 4)

AE	E1	E0	Error Type
0	0	No error	
1	1	0	Single check bit error
1	1	1	Single-data error
1	0	0	Double-bit error
	All Others		Invalid conditions

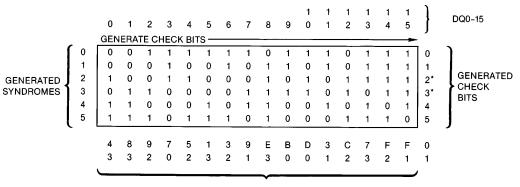
TABLE II. Error Flags after Normal Write (Mode 0)

AE	E1 (PE1)	E0 (PEO)	Error Type
0	1	1	No parity error
0	1	0	Parity error, byte 0
0	0	1	Parity error, byte 1
0	0	0	Parity error, bytes 0, 1

TABLE III. DP8400-2 Modes of Operation

TABLE III. Dr 0400-2 Modes of Operation											
Mode	M2 (R/W)	М1	МО	OES	Operation						
0	0	0	0	Х	Normal WRITE DIL $ ightarrow$ DOL, CG $ ightarrow$ COL $ ightarrow$ COB						
1	0	0	1	Х	$\begin{array}{c} \text{Complement WRITE} \\ \overline{\text{DIL}} \to \text{DOL}, \overline{\text{CIL}} \to \text{COL} \to \text{COB} \end{array}$						
2	0	1	0	Х	Diagnostic WRITE, DLE inhibited DQ8-DQ15 \oplus CG \rightarrow SOL \rightarrow SOB DQ8-DQ15 \rightarrow CIL \rightarrow COL \rightarrow COB						
3	0	1	1	Х	Complement data-only WRITE $\overline{\rm DIL} \to {\rm DOL},$ (CG0, 1, 4, 5, $\overline{\rm CG2}, \overline{\rm CG3}) \to {\rm COL} \to {\rm COB}$						
4	1	0	0	Х	Normal READ DIL \oplus DE \longrightarrow DOL, CIL \longrightarrow COL						
5	1	0	1	Х							
6A	1	1	0	0	READ generated syndromes, check bit bus, error flags, SG0-SG6 → DQ0-DQ6, CIL0-CIL6 → DQ8-DQ14, E1 → DQ7, E0 → DQ15						
6B	1	1	0	1	READ syndrome bus, check bit bus, error flags, SIL0-SIL6 \rightarrow DQ0-DQ6, CIL0-CIL6 \rightarrow DQ8-DQ14, E1 \rightarrow DQ7, E0 \rightarrow DQ15						
7A	1	1	1	0	Generated syndromes replace with zero $0 \rightarrow SIL \rightarrow SG$, $CIL \rightarrow COL$, $DIL \oplus DE \rightarrow DOL$						
7B	1	1	1	1	Generated syndromes replace SIL $ ightarrow$ SG, CIL $ ightarrow$ COL, DIL \oplus DE $ ightarrow$ DOL						

TABLE IV. Data-In To Check Bit Generate, Or Data Bit Error To Syndrome-Generate Matrix (16-Bit Configuration)



*C2, C3 generate odd parity

HEXADECIMAL EQUIVALENT OF SYNDROME BITS

Modes of Operation

There are three mode-control pins, M2, M1 and M0, offering 8 major modes of operation, according to Table III.

M2 is the READ/WRITE control. In normal operation, mode 0 is Normal WRITE and mode 4 is Normal READ. By clamping M0 and M1 low, and setting M2 low during WRITE and high during READ, the DP8400-2 is very easy to use for normal operation. The other modes will be covered in later sections

16-BIT CONFIGURATION

The first two rows on top of the check bit generate matrix (Table IV) indicate the data position of DQ0 to DQ15. The left side of the matrix, listed 0 to 5, corresponds to syndromes S0 to S5. S0 is the least significant syndrome bit. There are two rows of hexadecimal numbers below the matrix. They are the hex equivalent of the syndrome patterns. For example, syndrome pattern in the first column of the matrix is 001011. Its least significant four bits (0010) equal hexadecimal 4, and the remaining two bits (11) equal hexadecimal 3.

Check bit generation is done by selecting different combinations of data bits and generating parities from them. Each row of the check bit generate matrix corresponds to the generation of a check bit numbered on the right hand side of the matrix, and the ones in that row indicate the selection of data bits.

The following are the check bit generate equations for 16-bit wide data words:

- CG0 = DQ2 ⊕ DQ3 ⊕ DQ4 ⊕ DQ5 ⊕ DQ6 ⊕ DQ7 ⊕ DQ9 ⊕ DQ10 ⊕ DQ11 ⊕ DQ13 ⊕ DQ14 ⊕ DQ15
- $CG1 = DQ3 \oplus DQ6 \oplus DQ8 \oplus DQ9 \oplus DQ11 \oplus DQ13 \oplus DQ14 \oplus DQ15$

NE=no error

The following error map (Table V) depicts the relationship between all possible error conditions and their associated syndrome patterns. For example, if a syndrome pattern is S0-5=111101, data bit 14 is in error.

Figure 4 shows how to connect one DP8400-2 in a 16-bit configuration, in order to detect and correct single or double-bit errors. For a Normal WRITE, processor data is pre-

Cn=check bit n in error

sented to the DP8400-2, where it is fed through DIL0 and DIL1 to the check bit generator. This generates 6 parity bits from different combinations of data bits, according to Table IV. The numbers in the row below the table are the hexadecimal equivalent of the column bits (with bits 6, 7 low). A "1" in any row indicates that the data bit in that column is connected to the parity generator for that row. For example, check bit 1 generates parity from data bits 3, 6, 8, 9, 11, 13, 14, and 15.

Check bits 0, 1, 4, 5, and 6 generate even parity, and check bits 2 and 3 generate odd parity. This is done to insure that a total memory failure is detected. If all check bits were even parity, then all zeroes in the data word would generate all check bits zero and a total memory failure would not be detected when a memory READ was performed. Now allzero-data bits produce C2 and C3 high and a total memory failure will be detected. When reading back from the same location, the memory data bits (possibly in error) are fed to the same check bit generator, where they are compared to the memory check bits (also possibly in error) using 6 exclusive-OR gates. The outputs of the XORs are the syndrome bits, and these can be determined according to Table IV for one data bit error. For example, an error in bit 2 will produce the syndrome word 101001 (for S5 to S0 respectively). The syndrome word is decoded by the error encoder to the error flags, and the data-error decoder to correct a single data bit error. Assuming the memory data has been latched in the DIL, by making DLE go low, memory data can be disabled. Then by setting OBO and OB1 low, corrected data will appear on the data bus. The syndromes are available as outputs on pins S0-5 when OES is low. It is also possible to feed in syndromes to SIL when OES is high and CSLE goes high. This can be useful when using the Error Management Unit shown in Figure 4. C6 and S6 are not used for 16 bits. It is safe therefore to make C6 appear low, through a 2.7 $k\Omega$ resistor to ground. The same applies for S6 if syndromes are input to the DP8400-2. If OES is permanently low, S6 may be left open.

Any 16-bit memory correct system using the DP8400-2 without syndrome inputs must keep the $\overline{\text{OES}}$ pin grounded, then all the syndrome I/O pins may be left open. The reason for this is that the DP8400-2 resets the syndrome input latch at power up. If the $\overline{\text{OES}}$ pin is grounded, the syndrome input latch will remain reset for normal operations.

The parameter t_{NMR} (see Figure 10b), new mode recognized time, is measured from M2 (changing from READ to WRITE) to the valid check bits appearing on the check bit bus, provided the $\overline{\text{OLE}}$ was held low.

The parameter t_{MCR} (see Figure 10b), mode change recognized time, is measured from M2 (changing from WRITE to

D=two bits in error

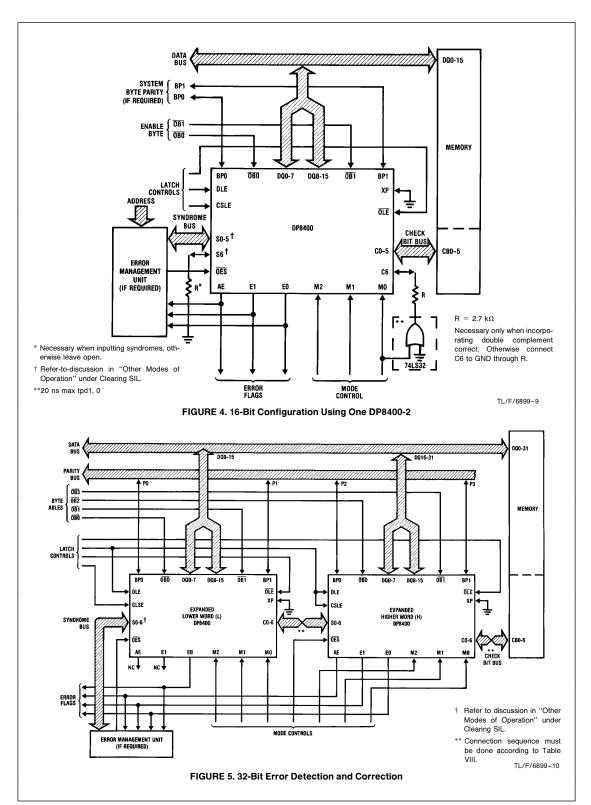
TABLE V.	Syndrome	Decode To	Bit In Error	For 16-Bit	Data Word
IADEL V.	Oynai onic	DCCCGGC 10	DIC III EII OI	101 10-01	Data Word

						,												
		S0	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1
Syndre	ome	S1	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1
Bits		S2	0	0	0	0	1	1	1	1	0	0	0	0	1	1	1	1
		S3	0	0	0	0	0	0	0	0	1	1	1	1	1	1	1	1
S5	S4																	
0	0		NE	C0	C1	D	C2	D	D	3	СЗ	D	D	9	D	10	Т	D
0	1		C4	D	D	11	D	Т	Т	D	D	7	Т	D	Т	D	D	15
1	0		C5	D	D	6	D	4	Т	D	D	2	Т	D	12	D	D	14
1	1		D	5	Т	D	0	D	D	13	1	D	D	Т	D	Т	8	D

Number = single data bit in error

T=three errors detected

^{*}CG2 and CG3 are odd parities.



Modes of Operation (Continued)

READ) when both E1 and E2 become invalid. This is required when a memory correcting system employs the DP8400-2 with byte parity checking. The E1 and E2 pins flag the byte parity error in a memory WRITE cycle. When the DP8400-2 switches to a subsequent memory READ cycle, it requires t_{MCR} for E1 and E2 to be switched to flag any READ error(s).

Expanded Operation

32-BIT CONFIGURATION

Figure 5 shows how to connect two DP8400-2s in cascade to detect single and double-bit errors, and to correct single-data errors. The same circuit will also correct double-bit errors once a double-error has been detected, provided at least one error is a hard error. The lower chip L is in effect a slave to the higher chip H, which controls the memory check bits and error reporting. The check bit bus of L is reordered and connected to the syndrome bus of H, as shown in Figure 5

In a Normal WRITE mode, referring to Figures 13a, 13b, and 13c, the 7 check bits generated from the lower 16 bits (CGL) are transferred via the COL to the COB of L, provided $\overline{\rm OLE}$ is high and M2 (R/ $\overline{\rm W}$) of L is low. These partial check bits from L then appear at SIL of H, so that with CSLE high, they combine with the 6 check bits generated in H with an overlap of one bit, to produce 7 check bits. With M2 (R/ $\overline{\rm W}$) of H low, these 7 check bits are output from COB to memory

A READ cycle may consist of DETECT ONLY or DETECT THEN CORRECT, depending on the system approach. In both approaches, L writes its partial check bits, CGL, to H as in WRITE mode. H develops the syndrome bits from CGL, CGH and the 7 check bits read from memory in CIL, H then outputs from its error encoder (EE) if there is an error. If corrected data is required, H already knows if it has a single-data error from its syndrome bits, but if not, it must transfer partial syndromes back to L. These partial syndromes PSH. (CGH XOR-ed with CIL), are stored in SOL of H. L must therefore change modes from WRITE to READ, while H outputs the partial syndromes from its SOB by setting OES low. The partial syndromes are fed into CIL of L and XOR-ed with CGL to produce syndrome bits at SGL. The data error decoder, DED, then corrects the error in L. The DED of H will already have corrected an error in the higher 16 bits. Only one error in 32 bits can be corrected as a single-data error, the chip with no error does not change the contents of its DIL when it is enabled in DOL. Table VI shows the 3 error flags of H, which become valid during the DETECT cycle. E0 of L becomes valid during the CORRECT cycle, so that the 4 flags provide complete error reporting.

TABLE VI. Error Flags After Normal READ (32-Bit Configuration)

AE (H)	E1 (H)	E0 (H)	E0 (L)*	Error Type
0	0	0	0	No error
1	1	0	0	Single-check bit error
1	1	1	0	Single-data bit error (H)
1	1	0	1	Single-data bit error (L)
1	0	0	0	Double-bit error
	All O	thers		Invalid conditions

*E0 (L) is valid after transfer of partial syndromes from higher to lower Equations for 32-bit expansion:

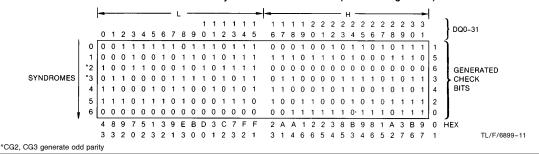
 $\begin{array}{rll} t_{DCB32} = & t_{DCB16} + t_{SCB16} \\ t_{DEV32} = & t_{DCB16} + t_{SEV16} \\ t_{DCD32} (High Chip) = & t_{DCB16} + t_{SCD16} \\ t_{DCD32} (Low Chip) = & t_{DCB16} + t_{BR}^* + t_{CCD16} \\ *_{t_{BR}: Bus reversing time (25 ns)} \end{array}$

32-BIT MATRIX

Table VII shows a 32-bit matrix using two DP8400-2s in cascade as in Figure 5. This is one of 12 matrices that work for 32 bits. The matrix for bits 0 to 15 (lower chip) is the matrix of Table IV for 16-bit configuration, with row 6 always "0". The matrix for bits 16 to 31 (higher chip) uses the same row combinations but interchanged, for example, the 3rd row (row 2) of L matrix is the same as the 6th row (row 5) of the H matrix. This means row 5 of H is in fact check bit 2 of H. Thus, the 6th row (row 5) combines generated check bit 5 (CG5) of L and generated check bit 2 of H. Check bit 5 of L therefore connects to the syndrome bit 2 (CG2) of H, and the composite generated check bit is written to check bit 2 of memory. Thus C2 performs a parity check on bits 0, 1, 2, 4, 5, 6, 8, 12, 13, 14, of L, and bits 16, 19, 20, 24, 26, 28, 29, 30, 31, of H. CG2 and CG3 generate odd parity, so that CG5 of L generates even parity which combines with CG2 of H generating odd parity. CG3 of L and CG3 of H both generate odd parity causing C3 to memory to represent even parity. Only 6 check bits are generated in each chip, the 7th (CG6) is always zero with XP grounded. Thus CG6 of L combines with CG0 of H so that C0 to memory is the parity of bits 18, 19, 20, 21, 22, 23, 25, 26, 27, 29, 30, 31. Similarly C6 to memory is only CG2 of L. The 7 composite generated check bits of H can now be written to memory.

When reading data and check bits from memory, CG6–CG0 of L are combined with CG6–CG0 of H in the same combination as WRITE. Memory check bits are fed into C6–C0 of H and compared with the 7 combined parity bits in H, to

TABLE VII. Data Bit Error To Syndrome-Generate Matrix (32-Bit Configuration)



Expanded Operation (Continued) TABLE VIII. Check Bit Port To Syndrome Port Interconnections For Expansion To 32 Bits

		L S	ЬC	H S	ΗC		
	S0	0	0	1	1	CO	
	S1	1	1	5	5	C1	
Syndrome I/O	S2	2	2	6	6	C2	Check Bit I/O
to	S3	3	3	3	3	C3	to
Management	S4	4	4	4	4	C4	Memory
	S5	5	5	2	2	C5	,
	S6	6	6	0	0	C6	

TABLE IX. Syndrome Decode To Bit In Error For 32-Bit Data Word

Syndr Bits	ome	S0 S1 S2 S3	0 0 0	1 0 0	0 1 0	1 1 0	0 0 1 0	1 0 1 0	0 1 1	1 1 1	0 0 0	1 0 0	0 1 0	1 1 0	0 0 1 1	1 0 1	0 1 1	1 1 1
S6	S5	S4		-	-	-	-	-	-	-		-						·
0	0	0	NE	C0	C1	D	C2	D	D	3	СЗ	D	D	9	D	10	Т	D
0	0	1	C4	D	D	11	D	Т	Т	D	D	7	17	D	Т	D	D	15
0	1	0	C5	D	D	6	D	4	Т	D	D	2	28	D	12	D	D	14
0	1	1	D	5	16	D	0	D	D	13	1	D	D	24	D	Т	8	D
1	0	0	C6	D	D	22	D	Т	Т	D	D	25	18	D	Т	D	D	Т
1	0	1	D	27	21	D	Т	D	D	Т	23	D	D	Т	D	Т	Т	О
1	1	0	D	19	20	D	Т	D	D	Т	26	D	D	30	D	Т	Т	D
1	1	1	Т	D	D	29	D	Т	Т	D	D	31	Т	D	Т	D	D	Т

NE = no error Number = single data bit in error

Cn=check bit n in error D=two bits in error

T=three errors detected

produce 7 syndrome bits S6-S0. H can now determine if there is any error, and if it has a single-data error, it can locate it and correct it without transferring partial syndromes to L. As an example of a DETECT cycle, CG5 of L combines with CG2 of H and is compared in H with memory check bit

If L is now set to mode 4, Normal READ, and OES of H is set low, the partial syndromes of H (CG6-CG0 of H XOR-ed with C6-C0 of H) are transferred and shifted to L. L receives these partial syndromes (S6-S0 of H) as check bit inputs C2, C1, C4, C3, C5, C0, C6 respectively, and compares them with CG6-CG0 respectively, to produce syndrome bits S6-S0. L now decodes these syndromes to correct any single-data error in data bits 0 to 15. For example, partial syndrome bit 2 of H combines with generated check bit 5 of L to produce syndrome bit 5 in L. An error in data bit 10 will create syndrome bits in L as 0001101 from S6-S0, and these will appear on S6-S0 of L with OES low. An error in H will appear as per the H matrix. For example, an error in bit 16 will cause S6-S0 of L to be 0110010.

If OES of L is set low, this syndrome combination appears on pins S6 to S0. For errors in bits 0 to 15, the syndrome outputs will be according to Table VII. For errors in bits 16 to 31, the syndrome outputs from L will still be according to Table VII due to the shifting of partial syndrome bits from H to L. The syndrome outputs from L are unique for each of the possible 32 bits in error.

If there is a check bit error, only one syndrome bit will be high. For example, if C5 is in error, then S1 of L will be high. For double-errors, an even number of syndrome bits will be high, derived from XOR-ing the two single-bit error syndromes. As mentioned previously, this is only one of the 12 approaches to connecting two chips for 32 bits, 6 of which are mirror images.

Table VIII depicts the exact connection for 32-bit expansion. LS equals syndrome bits of L. LC equals check bits of L. HS equals syndrome bits of H. HC equals check bits of H. Syndrome bits S0 to S6 of L are connected to system syndrome bits S0 to S6. LC and HS columns are lined together showing the check bit port of L connected to the syndrome port of H in the exact sequence as shown in Table VIII. For example, check bit C0 of L is connected to the syndrome bit S1 of H, and check bit C6 of L is connected to the syndrome bit S0 of H. Check bits of H are connected to the system check bits in the order shown. Check bit C1 of H is connected to the system check bit C0.

EXPANSION FOR DATA WORDS REQUIRING 8 CHECK BITS

For 16-bit and 32-bit configurations, XP is set permanently low. In 48-bit or 64-bit configurations, XP is either set permanently to V_{CC} or left open, according to Table X, to provide 8 check bits and syndrome bits.

TABLE X. XP: Expansion Status

XP	Status	Data Bus
0V	BP0 and BP1 are byte parity I/O CG6=0	< 40 Bits
Open	No byte parity I/O, CG6 and CG7 = word parity	≥ 40 Bits
V _{CC}	No byte parity I/O, CG6 and CG7 = 0	≥ 40 Bits

48-BIT EXPANSION

Three DP8400-2s are required for 48 bits, with the higher chip using all 8 of its check bits to the memory. No byte parity is available for 48 to 64 bits. XP of all three chips must be at V_{CC}. The three chips are connected in cascade as in

Expanded Operation (Continued)

TABLE XI. Check Bit Port To Syndrome Port Interconnections For Expansion To 48 Bits

		LL S	Ьς	IJs	Цc	Нs	Нc		
	S0	0	0	1	1	6	6	CO	
	S1	1	1	5	5	1	1	C1	
Syndrome I/O	S2	2	2	6	6	4	4	C2	Check Bit I/O
to	S3	3	3	3	3	7	7	C3	to
Management	S4	4	4	4	4	2	2	C4	Memory
Management	S5	5	5	2	2	3	3	C5	ivicitiony
	S6	6	6	0	0	5	5	C6	
	S7	7	7	7	7	0	0	C7	

For example: S0 of LL is connected to system syndrome S0, C0 of LL is connected to S1 of LH, C1 of LH is connected to S6 of HL. C6 of HL is connected to system check bit C0.

TABLE XII. Syndrome Decode To Bit In Error For 48-Bit Data Word

			S0	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1
	drome		S1	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1
Bits			S2	0	0	0	0	1	1	1	1	0	0	0	0	1	1	1	1
S 7	S6	S5	S3 S4	0	0	0	0	0	0	0	0	1	1	1	1	1	1	1	1
-5/	30	30	54								ı								I
0	0	0	0	NE	C0	C1	D	C2	D	D	3	C3	D	D	9	D	10	Т	D
0	0	0	1	C4	D	D	11	D	Т	Т	D	D	7	17	D	Т	D	D	15
0	0	1	0	C5	D	D	6	D	4	Т	D	D	2	28	D	12	D	D	14
0	0	1	1	D	5	16	D	0	D	D	13	1	D	D	24	D	Т	8	D
0	1	0	0	C6	D	D	22	D	Т	Т	D	D	25	18	D	Т	D	D	Т
0	1	0	1	D	27	21	D	32	D	D	Т	23	D	D	Т	D	Т	Т	D
0	1	1	0	D	19	20	D	33	D	D	Т	26	D	D	30	D	Т	Т	D
0	1	1	1	44	D	D	29	D	Т	40	D	D	31	Т	D	Т	D	D	Т
1	0	0	0	C7	D	D	Т	D	Т	43	D	D	Т	Т	D	Т	D	D	Т
1	0	0	1	D	Т	35	D	Т	D	D	Т	Т	D	D	Т	D	Т	Т	D
1	0	1	0	D	Т	41	D	39	D	D	Т	Т	D	D	Т	D	Т	Т	D
1	0	1	1	42	D	D	Т	D	Т	47	D	D	Т	Т	D	Т	D	D	Т
1	1	0	0	D	Т	38	D	37	D	D	Т	Т	D	D	Т	D	Т	Т	D
1	1	0	1	36	D	D	Т	D	Т	45	D	D	Т	Т	D	Т	D	D	Т
1	1	1	0	34	D	D	Т	D	Т	Т	D	D	Т	Т	D	Т	D	D	Т
1	1	1	1	D	Т	46	D	Т	D	D	Т	Т	D	D	Т	D	Т	Т	D

T = three errors detected

 $\begin{array}{ll} {\sf NE} = {\sf no} \; {\sf error} & {\sf Cn} = {\sf check} \; {\sf bit} \; {\sf n} \; {\sf in} \; {\sf error} \\ {\sf Number} = {\sf single} \; {\sf data} \; {\sf bit} \; {\sf in} \; {\sf error} \\ \end{array}$

Figure 6, but with the HH chip removed. The error flags are as Table XV, but with AE (HH) and E1 (HH) becoming AE (HL) and E1 (HL), and E0 (HH) removed.

The matrix for 48 bits is that for 64 bits shown (in Table XVI) but only using bits 0 to 47. This is one of many matrices for 48-bit expansion using the basic 16-bit matrix. The matrix shown uses 2 zeroes for CG6 and CG7, for all three chips, with XP set to $V_{\mbox{\footnotesize CC}}$. Other matrices may use CG6 and CG7 as word parity with XP open.

64-BIT EXPANSION

There are two basic methods of expansion to 64 bits, both requiring 8 check bits to memory, and four DP8400-2s. One is the cascade method of Figure 6, requiring no extra ICs. With this method partial check bits have to be transferred through three chips in the WRITE or DETECT mode, and partial syndrome bits transferred back through three chips in CORRECT mode. This method is similar to Figure 5, 32-bit approach. The connections between the check bit bus and syndrome bus for each of the chip pairs are shown in

The error flags of HH are valid during the DETECT cycle as in Table XV, and the other error flags are valid during the CORRECT cycle.

A faster method of 64-bit expansion shown in Figure 7 requires a few extra ICs, but can WRITE in 50 ns, DETECT in 42 ns or DETECT THEN CORRECT in 90 ns. In the WRITE mode, all four sets of check bits are combined externally in the 8 74S280 parity generators. These generate 8 composite check bits from the system data, which are then enabled to memory. In the DETECT mode, again 8 composite check bits are generated, from the memory data this time, and compared with the memory check bits to produce 8 external syndrome bits. These syndrome bits may be OR-ed to determine if there is any error. By making the 74S280 outputs SYNDROMES, then any bit low causes the 74S30 NAND gate to go high, giving any error indication. To correct the error, these syndrome bits are fed re-ordered into SIL of each DP8400-2 now set to mode 7B. This enables the syndromes directly to SG and then DED of each chip. One chip

Expanded Operation (Continued)

will output corrected data, while the other three output nonmodified data (but still correct).

Equations for fast 64-bit expansion:

 $t_{DCB64} \, = \, t_{DCB16} \, + \, t_{pd} \, (74S280) \, + \, t_{pd} \, (74S240)$ $t_{DEV64} = t_{DCB16} + t_{pd} (74S280) + t_{pd} (74S30)$ $t_{DCB64} = t_{DCB16} + t_{pd} (74S280) + t_{pd} (74ALS533)$

64-BIT MATRIX

With the 64-bit matrix shown in Table XVI, it is necessary to set at least one chip with CG6, CG7 non-zero. The highest chip, connected to data bits 48 to 63, has XP set open, so that its CG6 and CG7 are word parity. The syndrome word of the highest chip will now have either 5 or 7 syndrome bits high, but inside the chip CG6 and CG7 remove two of these in a READ so that the chip sees the normal 3 or 5 syndrome

TABLE XIII. Check Bit Port To Syndrome Port Interconnections For Expansion To 64 Bits

		LL S	C	LH S	LH C	HL S	HL C	HH S	HC		
Syndrome I/O to Management	S0 S1 S2 S3 S4 S5 S6 S7	0 1 2 3 4 5 6 7	0 1 2 3 4 5 6 7	1 5 6 3 4 2 0 7	1 5 6 3 4 2 0 7	6 1 4 7 2 3 5 0	6 1 4 7 2 3 5 0	7 0 1 2 3 4 5 6	7 0 1 2 3 4 5 6	C0 C1 C2 C3 C4 C5 C6 C7	Check Bit I/O to Memory

For example: S0 of LL is connected to system syndrome S0. C0 of LL is connected to S1 of LH. C1 of LH is connected to S6 of HL. C6 of HL is connected to S7 of HH. C7 of HH is connected to system check bit C0.

TABLE XIV. Syndrome Decode To Bit In Error For 64-Bit Data Word

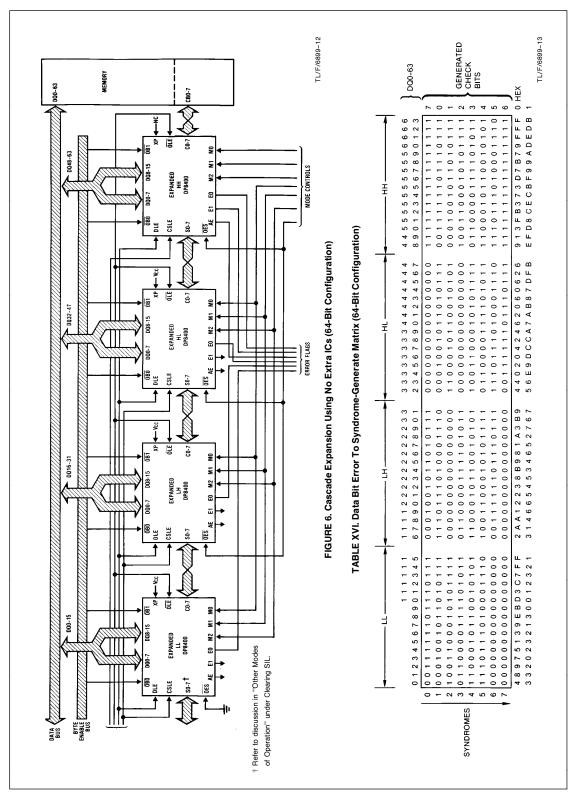
			S0	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1
Syn	drome	!	S1	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1
Bits			S2	0	0	0	0	1	1	1	1	0	0	0	0	1	1	1	1
			S3	0	0	0	0	0	0	0	0	1	1	1	1	1	1	1	1
S7	S6	S5	S4																
0	0	0	0	NE	C0	C1	D	C2	D	D	3	C3	D	D	9	D	10	Т	D
0	0	0	1	C4	D	D	11	D	Т	Т	D	D	7	17	D	Т	D	D	15
0	0	1	0	C5	D	D	6	D	4	Т	D	D	2	28	D	12	D	D	14
0	0	1	1	D	5	16	D	0	D	D	13	1	D	D	24	D	Т	8	D
0	1	0	0	C6	D	D	22	D	Т	Т	D	D	25	18	D	Т	D	D	Т
0	1	0	1	D	27	21	D	32	D	D	Т	23	D	D	Т	D	Т	Т	D
0	1	1	0	D	19	20	D	33	D	D	Т	26	D	D	30	D	Т	Т	D
0	1	1	1	44	D	D	29	D	Т	40	D	D	31	Т	D	Т	D	D	Т
1	0	0	0	C7	D	D	Т	D	Т	43	D	D	Т	Т	D	Т	D	D	51
1	0	0	1	D	Т	35	D	Т	D	D	57	Т	D	D	58	D	Т	Т	D
1	0	1	0	D	Т	41	D	39	D	D	59	Т	D	D	Т	D	Т	Т	D
1	0	1	1	42	D	D	55	D	Т	47	D	D	Т	Т	D	Т	D	D	63
1	1	0	0	D	Т	38	D	37	D	D	54	Т	D	D	52	D	Т	Т	D
1	1	0	1	36	D	D	50	D	Т	45	D	D	60	Т	D	Т	D	D	62
1	1	1	0	34	D	D	53	D	Т	Т	D	D	48	Т	D	Т	D	D	61
1	1	1	1	D	49	46	D	Т	D	D	Т	Т	D	D	Т	D	56	Т	D

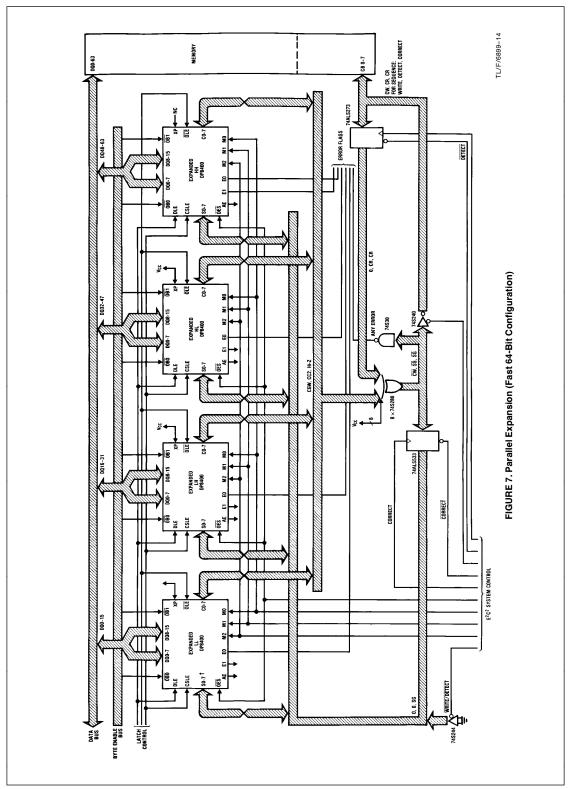
T = three errors detected

 $\begin{array}{ll} \text{NE} = \text{no error} & \text{Cn} = \text{check bit n in error} \\ \text{Number} = \text{single data bit in error} & \text{D} = \text{two bits in error} \\ \end{array}$

TABLE XV. Error Flags After Normal READ (Any 64-Bit Configuration)

AE (HH)	E1 (HH)	E0 (HH)	E0 (HL)	E0 (LH)	E0 (LL)	Error Type
0	0	0	0	0	0	No error
1	1	0	0	0	0	Single-check bit error
1	1	1	0	0	0	Single-data bit error in HH
1	1	0	1	0	0	Single-data bit error in HL
1	1	0	0	1	0	Single-data bit error in LH
1	1	0	0	0	1	Single-data bit error in LL
1	0	0	0	0	0	Double-error





Other Modes Of Operation

DOUBLE ERROR CORRECTION, USING THE DOUBLE-COMPLEMENT APPROACH

The DP8400-2 can be made to correct two errors, using no extra ICs or check bits, if at least one of the two errors detected is a hard error. This does require an extra memory WRITE and READ. Nevertheless, if a permanent failure exists, and an additional error occurs (creating two errors), both errors can be corrected, thereby saving a system crash.

Once a double error has been detected, the system puts the DP8400-2 in COMPLEMENT mode by setting M0 high. First a WRITE cycle is required and M2 is set low, putting the chip in mode 1, Table III, (COMPLEMENT WRITE), so that the contents of DIL are complemented into DOL, and the contents of CIL complemented into COL. $\overline{OB0}$ and $\overline{OB1}$ are set low so that complemented data and check bits can be written back to the same location of memory. Writing back complemented data to a location with a hard error forces

the error to repeat itself. For example, if cell N of a particular location is jammed permanently high, and a low is written to it, a high will be read. However, when the data is complemented a low is again written, so that a high is read back for the second time. After a second READ (this second READ is a COMPLEMENT READ) of the location, data and check bits from the memory are recomplemented, so that bit N now contains a low. In other words, the error in bit N has corrected itself, while the other bits are true again. If there are two hard errors in a location, both are automatically corrected and the DP8400-2 detects no error on COMPLE-MENT READ, as in Figure 8a. Figure 8b also shows that if one error is soft, the hard error will disappear on the second READ and the DP8400-2 corrects the soft error as a singleerror. Therefore, in both cases, the DOL contains corrected data, ready to be enabled by $\overline{\text{OB0}}$ and $\overline{\text{OB1}}$. A WRITE to memory at this stage removes the complemented data written at the start of the sequence.

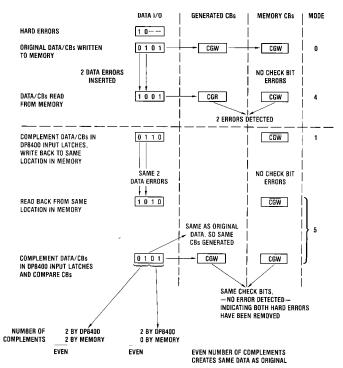


FIGURE 8a. Double Error Correct Complement Hard Error Method — 2 Hard Errors In Data Bits

Other Modes of Operation (Continued)

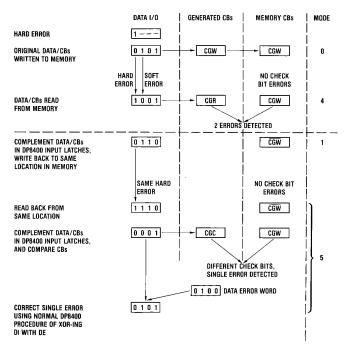


FIGURE 8b. Double Error Correct Complement Hard Error Method — 1 Hard Error, 1 Soft Error In Data Bits

The examples shown in Figures 8a and 8b are for 4 data bits. This approach will work for any number of data bits, but for simplicity these examples show how complementing twice corrects two errors in the data bits. The double COMPLEMENT approach also works for any two errors providing at least one is hard. In other words, one data-bit error and one check bit error, or two check bit errors are also corrected if one or both are hard. At the end of the COMPLEMENT READ cycle, the error flags indicate whether the data was correctable or not, as shown in Table XVII. If both the error were soft, then the data was not correctable and the error flags indicate this.

This approach is ideal where double errors are rare but may occur. To avoid a system crash, a double-error detect now causes the system to enter a subroutine to set the DP8400-2 in COMPLEMENT mode. This method is also useful in bulk-memory applications, where RAMs are used with known cell failures, and is applicable in 16, 32, 48 or 64-bit

configuration. In the 16-bit configuration, modes 1 and 5 of Table III are used. In the 32-bit expanded configuration, modes 1, 5 and 5 are used for the highest chip, and modes 3, 3 and 4 for the lower chip for WRITE, DETECT, and CORRECT. With the lower chip it is necessary to wrap around DOL (after latching its contents in mode 3), back to DIL and perform a Normal READ in mode 4 in the lower chip.

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TABLE XVII. ERROR FLAGS AFTER COMPLEMENT READ (MODE 5)

AE	E1	E0	Error Type
0	0	0	Two hard errors
1	1	0	One hard error, one soft check bit error
1	1	1	One hard error, one soft data bit error
1	0	0	Two soft errors, not corrected

Other Modes of Operation (Continued)

DOUBLE-ERROR CORRECT WITH ERROR LOGGING

Figures 4 and 5 show the E²C² syndrome port connected to an error management unit (EMU). This scheme stores syndromes and the address of locations that fail, thereby logging the errors. Subsequent errors in a memory location that has already stored syndromes in the EMU, can then be removed by injecting the stored syndromes of the first error. To save the addresses and syndromes when power to the EMU is removed, it is necessary to be able to transfer information via the E²C² syndrome port to the processor data bus. This is also useful for logging the errors in the processor. Transfer in the opposite direction is also necessary.

DATA BUS TO SYNDROME BUS TRANSFER

This is necessary when transferring syndrome information to the error management unit, which is connected to the external syndrome bus. First, data to make CG = 0 (all data bits high) must be latched in DIL. Then in mode 2, data is fed to CIL, XOR-ed with 0, and output via SOL with $\overline{\text{OES}}$ low to the syndrome bus. Data is therefore fed directly from the system to the syndrome bus, and this cycle may be repeated as long as DLE is kept low, forcing CG to remain zero.

SYNDROME BUS TO DATA BUS TRANSFER

This is important when information in the error logger or error management unit has to be read. The DP8400-2 is set to mode 6B with $\overline{\text{OES}}$ high, and with $\overline{\text{OBO}}$, $\overline{\text{OB1}}$ and $\overline{\text{OLE}}$ low. If CSLE is high, the syndrome bus and check bit bus data appear on the lower and upper bytes of the data bus to be read by the system. Also E1 and E0 values that were valid when mode 6 was entered, appear on DQ7 and DQ15.

FULL DIAGNOSTIC CHECK OF MEMORY

Using mode 2, it is possible to transfer the upper byte of the data bus directly to the CIL, with CSLE high, without affecting DIL. These simulated check bits then appear on the check bit bus with $\overline{\text{OLE}}$ low, which also causes the previously latched contents of DIL to transfer to DOL. By enabling $\overline{\text{OB0}}$ and $\overline{\text{OB1}}$ data can be written to memory with the simulated check bits. A Normal READ cycle can then aid the system in determining that the memory bits are functioning correctly, since the processor knows the check bits and data it sent to the E²C². Another solution is to put the E²C² in mode 6 and read the memory check bits directly back to the processor.

SELF-TEST OF THE E2C2 ON-CARD

Again using mode 2, data written from the processor data bus upper byte to CIL may be stored in CIL, by taking CSLE low. Next, a mode 0 WRITE can be performed and the user generated data can be latched in the DP8400-2 input latches (DLE held low). Now the user may perform a normal mode 4 READ. This will in effect be a Diagnostic READ of the user generated data and check bits without using the external memory. Thus by reading corrected data in mode 4, and by reading the generated syndromes, and error flags E0 and E1, the DP8400-2 can be tested completely on-card without involving memory.

MONITORING GENERATED SYNDROMES AND MEMORY CHECK BITS

Mode 6A enables SG0-SG6 onto DQ0-DQ6, and CILO-CIL6 onto DQ8-DQ14, provided OLE, OBO and OB1 are low. Also the two error flags, E1 and E0 (latched from the previous READ mode), appear on DQ7 and DQ15. This may be used for checking the internal syndromes, for reading the memory check bits, or for diagnostics by checking the latched error flags.

CLEARING SIL

In the 16-bit only configuration, or the lower chip of expanded configurations, and in various modes of operation in the higher expanded chips, it is required that SIL be maintained at zero. At power-up initialization, both SIL and DIL are reset to all low. If $\overline{\text{OES}}$ is kept low, SIL will remain reset because CSLE is inhibited to SIL. Another method is to keep $\overline{\text{OES}}$ always high and the syndrome bus externally set low, or set low whenever CSLE can be used to clear SIL.

Mode 7A also forces the SIL to be cleared whenever CSLE occurs, and also these zero syndromes go to the internal syndrome bus SG. This puts the DP8400-2 in a PASS-THROUGH mode where the DIL contents pass to DOL and CIL contents to COL, if $\overline{\rm OLE}$ is low.

POWER-UP INITIALIZATION OF MEMORY

Both SIL and DIL are reset low at power-up initialization. This facilitates writing all zeroes to the memory data bits to set up the memory. The check bits corresponding to all-zero data will appear on the check bit bus if the DP8400-2 is set to mode 0 and $\overline{\text{OLE}}$ is set low. All-zero data appears on the data bus when $\overline{\text{OB0}}$ and $\overline{\text{OB1}}$ are also set low. The system can now write zero-data and corresponding check bits to every memory location.

BYTE WRITING

Figure 14a shows the block diagram of a 16-bit memory correction system consisting of a DP8400-2 error correction chip and a DP8409A DRAM controller chip. There are 12 control signals associated with the interface. Six of the signals are standard DP8400-2 input signals, three are standard DP8409A input signals, and three are buffer control signals. The buffer control signals, PBUF0 and PBUF1, control when data words or bytes from the DP8400-2/memory data bus are gated to the processor bus and when data words or bytes from the processor are gated to the DP8400-2/memory data bus.

When the processor is reading or writing bytes to memory, words will always be read or written by the DP8400-2 and DP8409A error correction and DRAM controller section. The High Byte Enable and Address Data Bit Zero signals from the processor should control the byte transfers via the ocal bus transceiver signals PBUF0 and PBUF1. The buffer control signal, DOUTB, controls when data from memory is gated onto the DP8400-2/memory data bus.

Figure 14b shows the timing relationships of the 12 control signals, along with the DP8400-2/memory data bus and some of the DRAM control signals (\overline{RAS} and \overline{CAS}). RGCK is the \overline{RAS} generator clock of the DP8409A which is used in Mode 1 (Auto Refresh mode), along with being the system clock.

Other Modes of Operation (Continued)

Having two separate byte enable pins, $\overline{\text{OB0}}$ and $\overline{\text{OB1}}\text{, it is}$ easy to implement byte writing using the DP8400-2. First it is necessary to read from the location to which the byte is to be written. To do this the DP8400-2 is put in normal Read mode (Mode 4), which will detect and correct a single bit error. WIN is kept high and RASIN is pulled low, causing the DP8409A, now in Mode 5 (Auto Access mode), to start a read memory cycle. The data word and check bits from memory are then enabled onto the DP8400-2/memory data bus by pulling DOUTB low. The data and check bits are valid on the bus after the \overline{RASIN} to \overline{CAS} time (t_{RAC}) plus the column access time (t_{CAC}) of the particular memories used. DLE, CSLE can then be pulled low in order to latch the memory data into the input latches of the DP8400-2. OLE can be pulled low to enable the corrected memory word, or the original memory word if no error was present, into the data output latches. Following this, DOUTB can be pulled high to disable the memory data from the DP8400-2/memory data bus. The corrected memory word will be available at the data output latches "tDCD16" after the memory word was available at the data input latches. Once the corrected data is available at the output latches OLE can be pulled high to latch the corrected data. Also DLE and CSLE can be pulled high in order to enable the input data latches again.

Now the DP8400-2 can be put into a write cycle (Mode 0 = M2 = Low). At this time the byte to be written to memory and the other byte from memory can be enabled onto the DP8400-2/memory data bus (\overline{OBO} , $\overline{PBUF1}$ or $\overline{OB1}$, $\overline{PBUF0}$ go low). DLE, CSLE can now transition low to latch the new memory word into the data input latch. \overline{OLE} is pulled low to enable the output latches. When the new checkbits are valid, t_{DCB16} after the data word is valid on the DP8400-2/memory data bus, \overline{OLE} and \overline{DLE} can be pulled high to latch the new memory word into the output latches, and then \overline{WIN} can be pulled low to write the data into memory. \overline{RASIN} should be held low long enough to cause the new data and check bits to be stored into memory (\overline{WIN}) data hold time).

Also a READ-MODIFY-WRITE cycle was performed, taking approximately 40% longer than a normal memory WRITE cycle. A READ and then a WRITE memory cycle could have been used in the above example but it would have taken longer.

Buffers are used in this system (74ALS244) to keep the Data Out and Data In of the memory IC's from conflicting with each other during Read-Modify-Write cycles.

A byte READ from memory is no different from a normal READ. This approach may be used for a 16-bit processor using byte writing, or an 8-bit processor using a 16-bit memory to reduce the memory percentage of check bits, or with memory word sizes greater than two bytes.

An APP NOTE (App Note 387) has been written detailing an Error Correcting Memory System using the DP8409A or DP8419 (Dynamic RAM Controller) and the DP8400-2 interfaced to a National Semiconductor Series 32000 CPU. See this App Note for further system details and considerations.

BEYOND SINGLE-ERROR CORRECT

With the advent of larger semiconductor memories, the frequency of the soft errors will increase. Also some memory system designers may prefer to buy less expensive memories with known cell, row or column failures, thus, more hard errors. All this means that double-error correct, triple-error detect capability, and beyond will become increasingly important. The DP8400-2 can correct two errors, provided one or both are hard errors, with no extra components, using the double complement approach. There are two other approaches to enhance reliability and integrity. One is to use the error management unit to log errors using the syndrome bus, and then to output these syndromes, when required, back to the DP8400-2.

DOUBLE SYNDROME DECODING

The other approach takes advantage of the Rotational Syndrome Word Generator matrix. This matrix is an improvement of the Modified Hamming-code, so that if, on a second DP8400-2, the data bus is shifted or rotated by one bit, and 2 errors occur, the syndromes for this second chip will be different from the first for any 2 bits in error. Both chips together output a unique set of syndromes for any 2 bits in error. This can be decoded to correct any 2-bit error. This is not possible with other Modified Hamming-code matrices.

Absolute Maximum Ratings (Note 1)

Maximum Power Dissipation at 25°C

Molded Package 3269 mW Lead Temperature (Soldering, 10 seconds) 300°C

*Derate molded package 26.2 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
V _{CC} , Supply Voltage	4.75	5.25	V
T _A , Ambient Temperature	0	70	°C

Electrical Characteristics (Note 2) $V_{CC} = 5V \pm 5\%$, $T_A = 0$ °C to 70°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{IL}	Input Low Threshold				0.8	V
V _{IH}	Input High Threshold		2.0			V
V _C	Input Clamp Voltage	$V_{CC} = Min, I_C = -18 \text{ mA}$		-0.8	-1.5	V
I _{IH}	Input High Current	$V_{IN} = 2.7V$		1	160	μΑ
I _{IH} (XP)	Input High Current	$V_{CC} = Max, XP = 5.25V$		2.5	4.5	mA
I _{IL} (XP)	Input Low Current	V _{CC} = Max, XP = 0V		-2.5	-4.5	mA
I _{IL} (BP0/C7)	Input Low Current	$V_{CC} = Max, V_{IN} = 0.5V$		-100.0	-500	μΑ
I _{IL} (BP1/S7)	Input Low Current	$V_{CC} = Max, V_{IN} = 0.5V$		-100.0	-500	μΑ
I _{IL} (CSLE)	Input Low Current	$V_{CC} = Max, V_{IN} = 0.5V$		-150.0	-750	μΑ
I _{IL} (DLE)	Input Low Current	$V_{CC} = Max, V_{IN} = 0.5V$		-200.0	-1000	μΑ
I _{IL}	Input Low Current	$V_{CC} = Max, V_{IN} = 0.5V$		-50.0	-250	μΑ
I _I	Input High Current (Max)	V _{IN} = 5.5V (Except XP Pin)			1.0	mA
V _{OL}	Output Low Voltage	I _{OL} = 8 mA (Except BP0, BP1) I _{OL} = 4 mA (BP0, BP1 Only)		0.3 0.3	0.5 0.5	V
V _{OH}	Output High Voltage	$I_{OH} = -100 \mu\text{A}$ $I_{OH} = -1 \text{mA}$	2.7 2.4	3.2 3.0		V V
los	Output Short Current (Note 3)	V _{CC} = Max		-150	-250	mA
Icc	Supply Current	V _{CC} = Max		220	300	mA
C _{IN} (I/O)	Input Capacitance All Bidirectional Pins	Note 4		8.0		pF
C _{IN}	Input Capacitance All Unidirectional Input Pins	Note 4		5.0		pF

Note 1: "Absolute Maximum Ratings" are the values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All typical values are for $T_A\!=\!25^{\circ}C$ and $V_{CC}\!=\!5.0V$

Note 3: Only one output at a time should be shorted.

Note 4: Input capacitance is guaranteed by periodic testing. F test=10 kHz at 300 mV, T_A =25°C.

Note 5: All switching parameters measured from 1.5V of input to 1.5V of output. Input pulse amplitude 0V to 3V, $t_f = t_f = 2.5$ ns.

DP8400-2 Switching Characteristics (Note 5) $V_{CC}=5.0V~\pm5\%,\,T_A=0^{\circ}C$ to $70^{\circ}C,\,C_L=50$ pF

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{DCB16}	Data Input Valid to Check Bit Valid	Figure 9b		29	40	ns
^t DEV16	Data Input to Any Error Valid	Figures 10b, 11b (Note 1)		21	31	ns
t _{DCD16}	Data Input Valid to Corrected Data Valid	Figure 10b, OB0, OB1 Low		44	61	ns
t _{DSI}	Data Input Set-Up Time Before DLE, CSLE H to L	Figures 10b, 13d	10	5		ns
t _{DHI}	Data Input Hold Time After DLE, CSLE H to L	Figures 10b, 13d	10	5		ns
t _{DSO}	Data Input Set-Up Time Before OLE L to H	Figure 10b	10	5		ns
t _{DHO}	Data Input Hold Time After OLE L to H	Figure 10b	10	5		ns
t _{DE0}	Data in Valid to E0 Valid	Figures 9b, 10b, 13d		36	55	ns
t _{DE1}	Data in Valid to E1 Valid	Figures 9b, 10b, 13d		43	55	ns
t _{IEV}	DLE, CSLE High to Any Error Flag Valid (Input Data Previously Valid)	Figure 10b		28	45	ns
^t IEX	DLE, CSLE High to Any Error Flag Invalid	Figures 9b, 10b		38	60	ns
t _{ILE}	DLE, CSLE High Width to Guarantee Valid Data Latched	Figures 10b, 13d	20			ns
t _{OLE}	OLE Low Width to Guarantee Valid Data Latched	Figure 13d	20			ns
t _{ZH}	High Impedance to Logic 1 from OBO, OB1, OES M2 H to L	Figures 9b, 10b, 13d		22	36	ns
t _{HZ}	Logic 1 to High Impedance from OBO , OB1 , OES , M2 L to H	Figures 9b, 10b, 13d,		38	55	ns
t _{ZL}	High Impedance to Logic 0 from OB0, OB1, OES M2 H to L	Figures 9b, 10b, 13d		19	35	ns
t _{LZ}	Logic 0 to High Impedance from OB0 , OB1 , OES , M2 H to L	Figures 9b, 10b, 13d		15	25	ns
t _{PPE}	Byte Parity Input Valid to Parity Error Flags Valid	Figure 9b		16	27	ns
t _{DPE}	Data In Valid to Parity Error Flags Valid	Figures 9b, 13d		27	55	ns
t _{DCP}	Data in Valid to Corrected Byte Parity Output Valid	Figure 9b		44	61	ns

Note 1: This parameter value holds given that an error occurred. In the case of no error, t_{DEV16} will be max of 80 ns.

DP8400-2 Switching Characteristics (Continued) (Note 5)

 $V_{CC}=$ 5.0V \pm 5%, $T_A=$ 0°C to 70°C, $C_L=$ 50 pF

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{NMR}	New Mode Recognize Time	Figure 10b		22	35	ns
t _{CDV}	Mode Valid to Complement Data Valid	Figure 11b		34	50	ns
t _{CCV}	Mode Valid to Complement Check Bit Valid	Figure 11b		30	45	ns
t _{SCB}	Syndrome Input Valid to Check Bit Valid	Figure 13d		20	35	ns
t _{SEV}	Syndrome Input Valid (CGL) to Any Error Valid	Figure 13d		17	27	ns
t _{SCD}	Syndrome Inputs Valid to Corrected Data Valid	Figure 13d		35	50	ns
t _{DSB}	Data Input Valid to Syndrome Bus Valid	Figure 13d, OES Low		28	46	ns
t _{CSB}	Check Bit Inputs Valid to Syndrome Bus Valid	Figure 13d, OES Low		19	32	ns
t _{CEV}	Check Bit Inputs Valid (PSH) to Any Error Valid	Figure 13d		17	30	ns
t _{CCD}	Check Bit Input Valid (PSH) to Corrected Data Valid	Figure 13d		30	45	ns
t _{DCB32}	Data Input Valid to Check Bit Valid	Figure 13d		49	75	ns
t _{DEV32}	Data Input Valid to Any Error Valid	Figure 13d		46	67	ns
t _{DCD32}	Data Input Valid to Corrected Data Out	Figure 13d, OB0, OB1 Low		84	110	ns

Note 1: "Absolute Maximum Ratings" are the values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All typical values are for $T_A\!=\!25^{\circ}\text{C}$ and $V_{CC}\!=\!5.0\text{V}.$

Note 3: Only one output at a time should be shorted.

Note 4: Input capacitance is guaranteed by periodic testing. F test=10 kHz at 300 mV, T_A =25°C.

 $\textbf{Note 5:} \ \text{All switching parameters measured from 1.5V of input to 1.5V of output. Input pulse amplitude 0V to 3V, } \\ t_f = t_f = 2.5 \ \text{ns.}$

Typical Applications

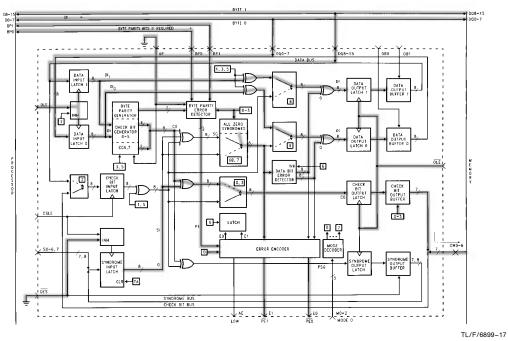


FIGURE 9a. DP8400-2 16-Bit Configuration, Normal WRITE with Byte Parity Error Detect If Required

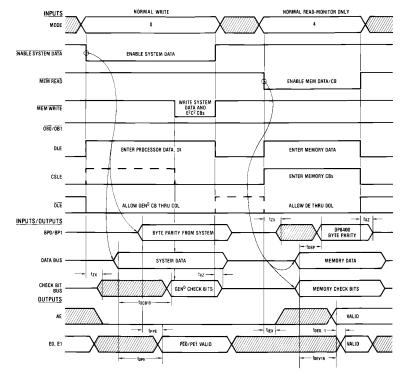


FIGURE 9b. DP8400-2 16-Bit Configuration, Normal WRITE and Normal READ Timing Diagram

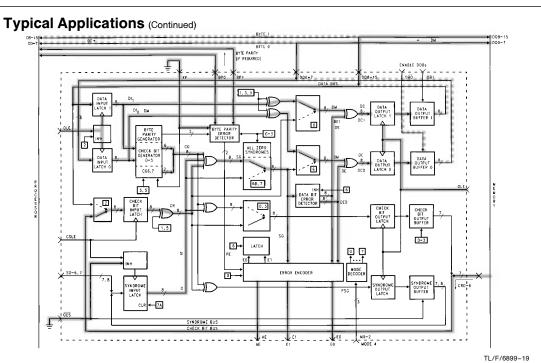
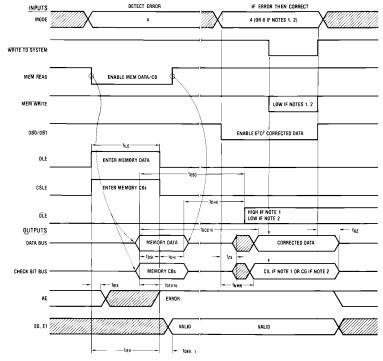


FIGURE 10a. DP8400-2 16-Bit Configuration, Normal READ — Detect Error (And Correct if Required---)



Note 1: If rewriting correct data and CBs to same location and single data error was detected.

Note 2: If rewriting correct data and CBs to same location and single check bit was detected.



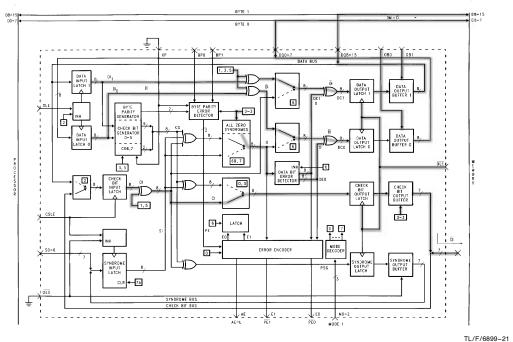
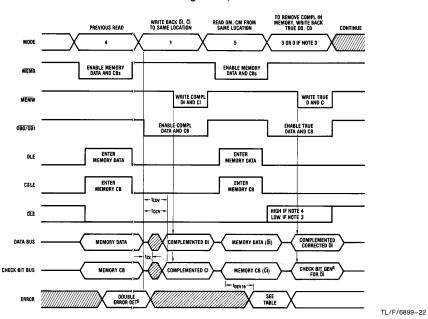


FIGURE 11a. DP8400-2 16-Bit Configuration, COMPLEMENT WRITE

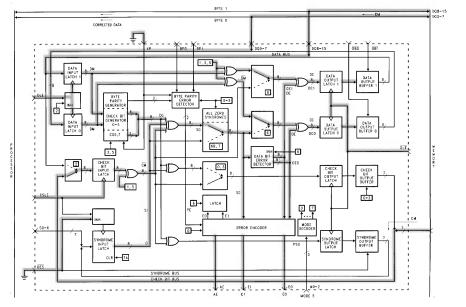


Note 3: If rewriting corrected data and CBs back to same location and 1 soft data bit error was detected.

Note 4: If rewriting corrected data and CBs back to same location and 2 hard errors or 1 soft check bit was detected.

FIGURE 11b. DP8400-2 16-Bit Configuration, Detect 2 Errors, COMPLEMENT WRITE, COMPLEMENT READ, Output Corrected Data Timing Diagram

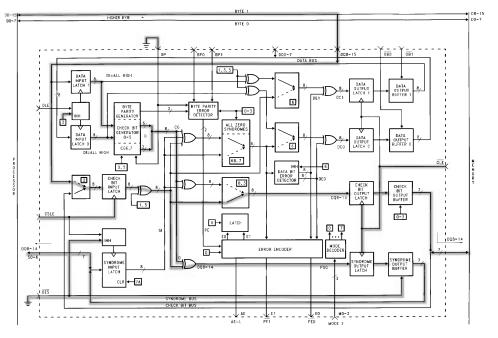
Typical Applications (Continued)



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FIGURE 11c. DP8400-2 16-Bit Configuration, COMPLEMENT READ and Output Corrected if One or Two Hard Errors

Typical Applications (Continued)



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FIGURE 12a. DP8400-2 16-Bit Configuration, Diagnostic WRITE, READ. Data Bus to Check Bit Bus or Syndrome Bus (Providing DI = HIGH in Previous Cycle to Set CG = All Zero For Transfer to S)

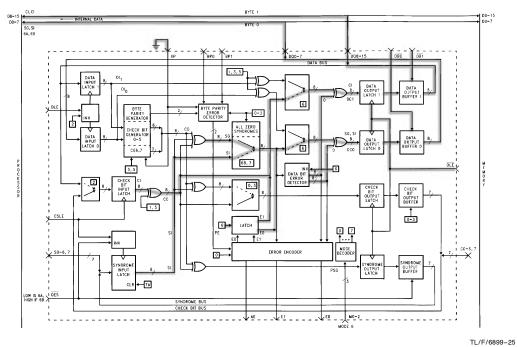
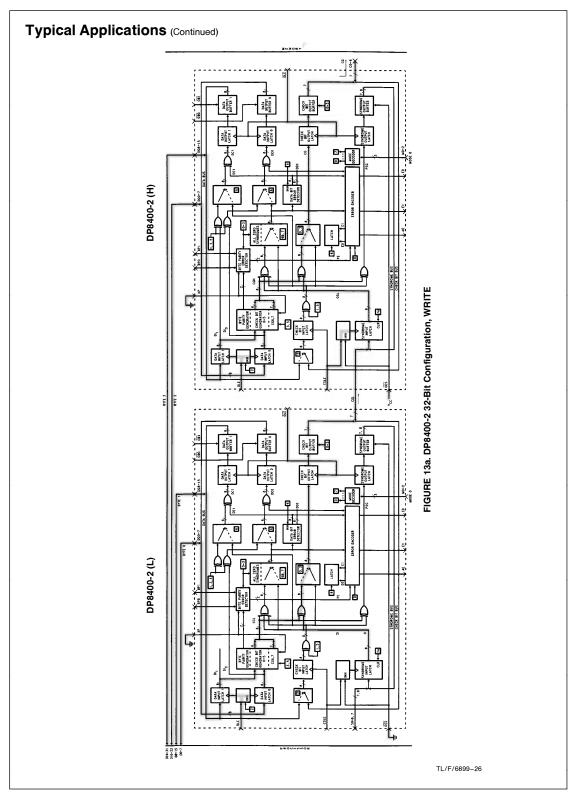
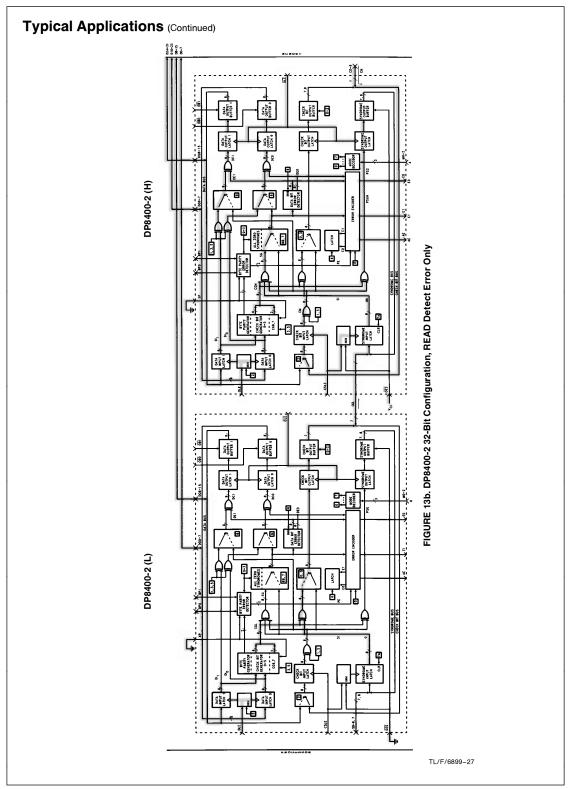
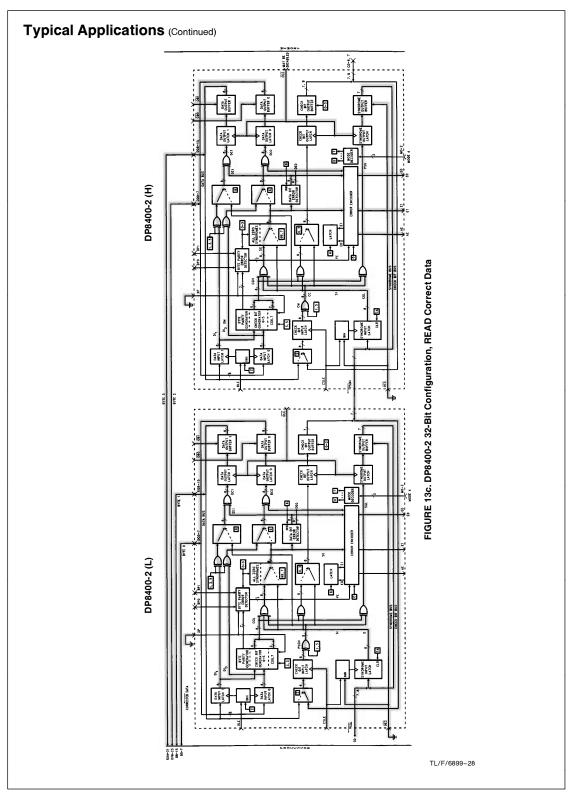
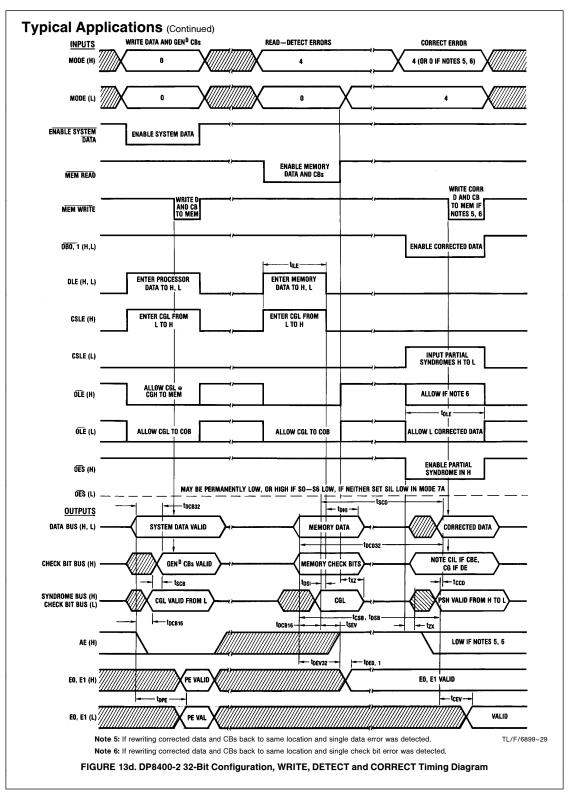


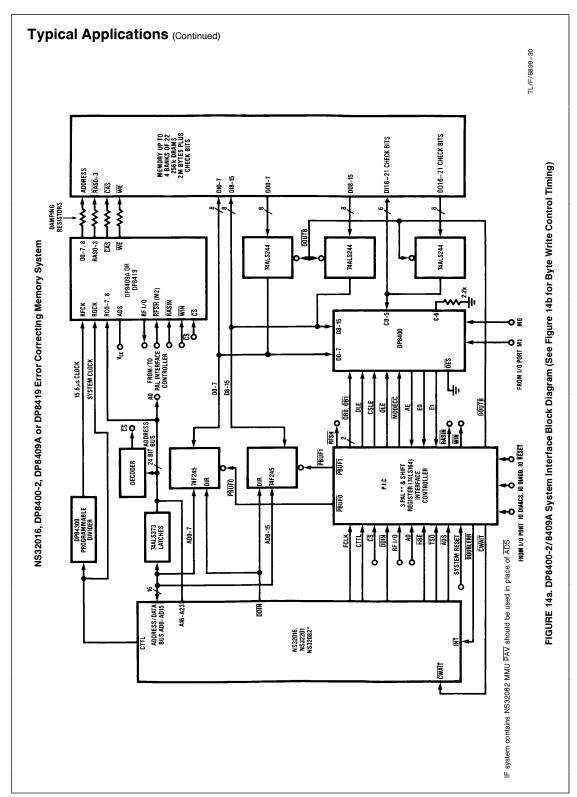
FIGURE 12b. DP8400-2 16-Bit Configuration, Monitor on Data Bus — Memory Check Bits

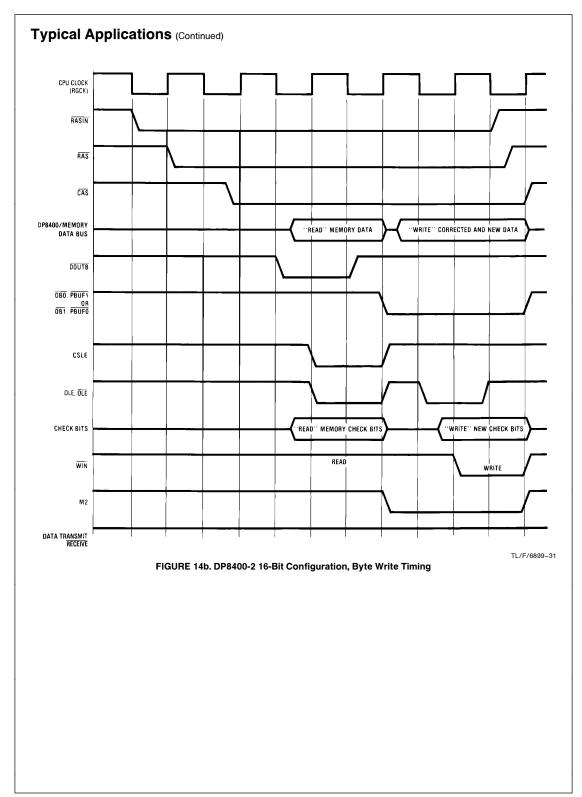












Typical Applications (Continued)

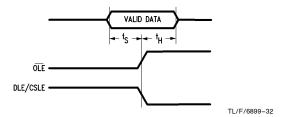


FIGURE 15. Timing Waveform for Set-Up and Hold Time

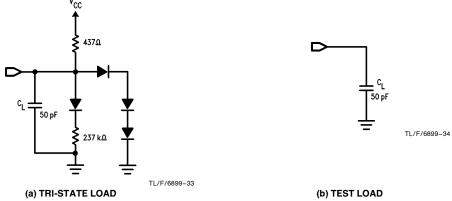
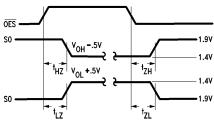
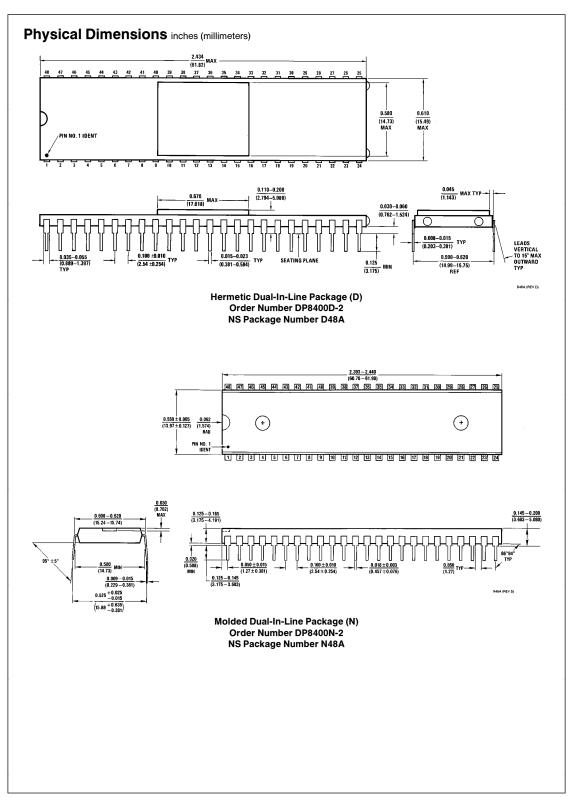


FIGURE 16. Loading Circuit

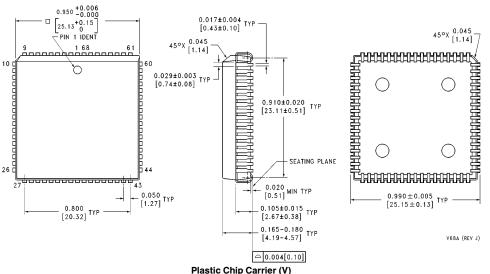


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FIGURE 17. TRI-STATE Measurement



Physical Dimensions inches (millimeters) (Continued)



Plastic Chip Carrier (V) Order Number DP8400V-2 NS Package Number V68A

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